

LAPT

2SA1186

Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2837)

Application : Audio and General Purpose

Absolute maximum ratings (Ta=25°C)

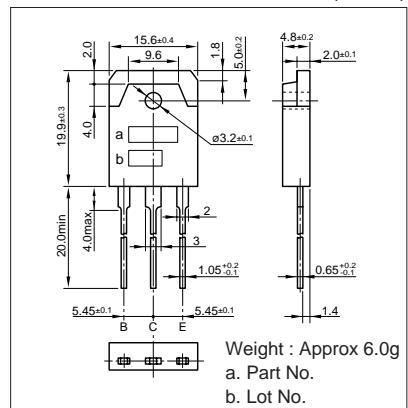
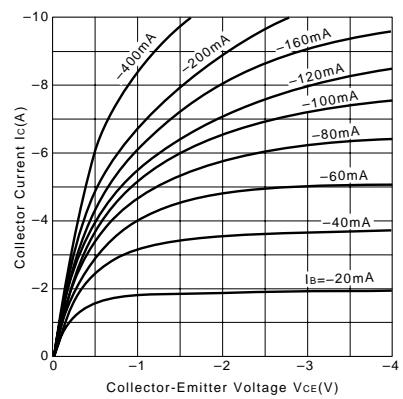
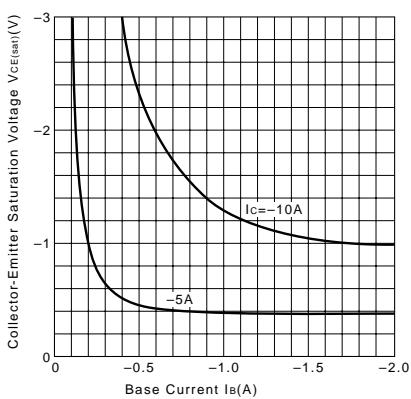
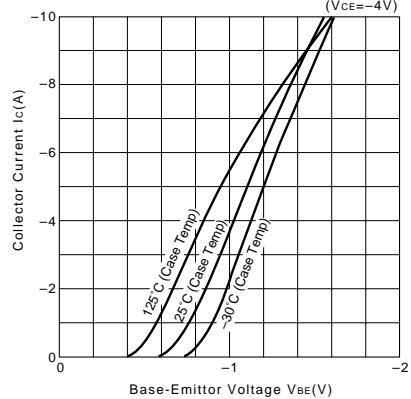
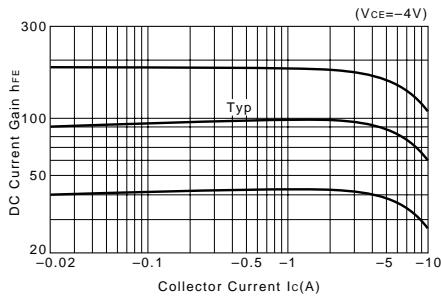
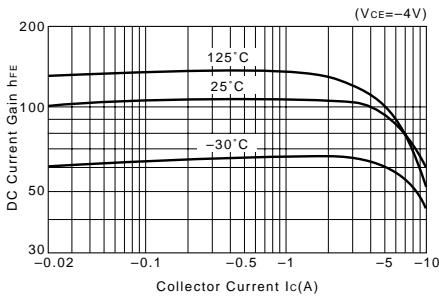
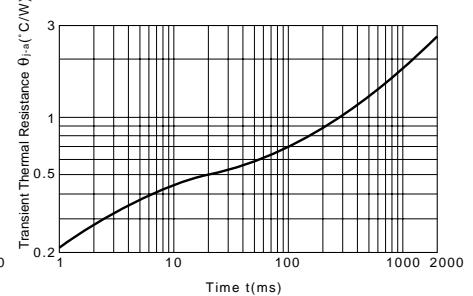
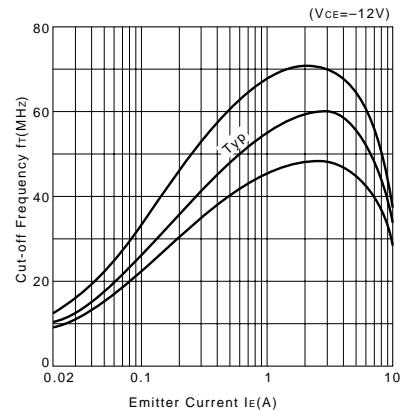
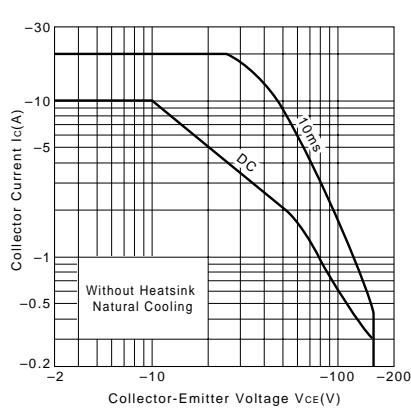
Symbol	Ratings	Unit
V _{CBO}	-150	V
V _{CEO}	-150	V
V _{EBO}	-5	V
I _c	-10	A
I _b	-2	A
P _c	100(Ta=25°C)	W
T _j	150	°C
T _{tsg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Ratings	Unit
I _{CBO}	V _{CB} =-150V	-100max	μA
I _{EBO}	V _{EB} =-5V	-100max	μA
V _{(BR)CEO}	I _c =-25mA	-150min	V
h _{FE}	V _{CE} =-4V, I _c =-3A	50min*	
V _{CE(sat)}	I _c =-5A, I _b =-0.5A	-2.0max	V
f _T	V _{CE} =-12V, I _e =1A	60typ	MHz
C _{OB}	V _{CB} =-80V, f=1MHz	110typ	pF

*h_{FE} Rank O(50to100), P(70to140), Y(90to180)**Typical Switching Characteristics (Common Emitter)**

V _{CC} (V)	R _L (Ω)	I _c (A)	V _{B2} (V)	I _{b1} (mA)	I _{b2} (mA)	t _{on} (μs)	t _{tsg} (μs)	t _f (μs)
-60	12	-5	5	-500	500	0.25typ	0.8typ	0.2typ

External Dimensions MT-100(TO3P)**I_c-V_{CE} Characteristics (Typical)****V_{CE(sat)}-I_b Characteristics (Typical)****I_c-V_{BE} Temperature Characteristics (Typical)****h_{FE}-I_c Characteristics (Typical)****h_{FE}-I_c Temperature Characteristics (Typical)****θ_{j-a}-t Characteristics****f_T-I_e Characteristics (Typical)****Safe Operating Area (Single Pulse)****Pc-Ta Derating**